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# Modeling Self Heating using HICUM

by  
Jörg Berkner, Infineon Technologies AG  
Munich, Germany

# Pulsed S-parameter measurement procedure using the HP85124 system

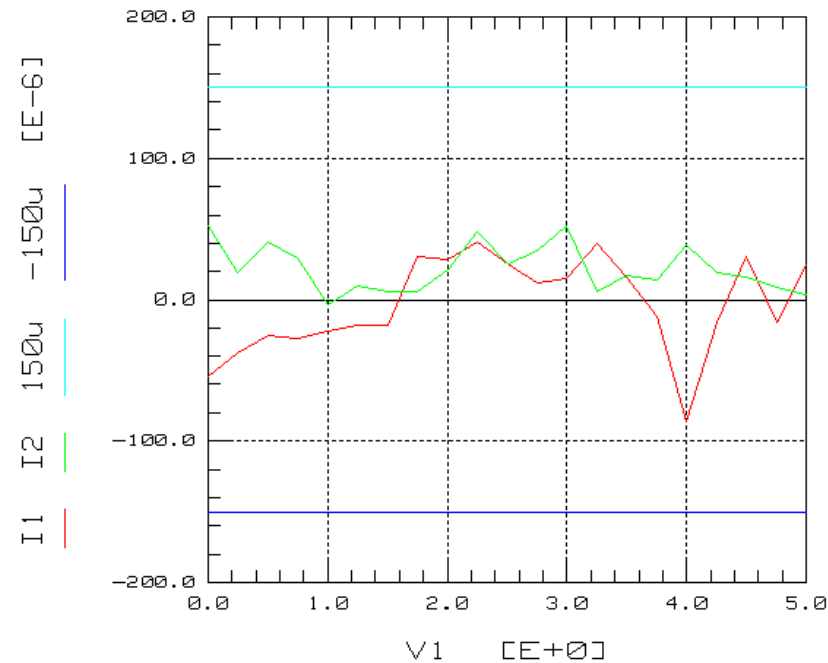
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- DC calibration: correction of ohmic losses and delays in the system, data are stored in file pulse.cal
- Measurement of the DC noise level with probes in air: noise level should be smaller than 100  $\mu\text{A}$
- Non-pulsed forward gummel measurement and non-pulsed forward output measurement,  $I_B$  – and  $V_B$  – driven, to evaluate the possible operating range of the device
- Measurement of  $I_C(t)$  to find out the right pulse period, pulse width and the RF measurement trigger time point
- Pulsed forward output measurement,  $V_B$  – driven
- Non-Pulsed S-parameter measurement,  $V_B$  – driven
- Check for the maximum possible RF input power
- Pulsed S-parameter measurement,  $V_B$  – driven

# Measurement of DC noise level

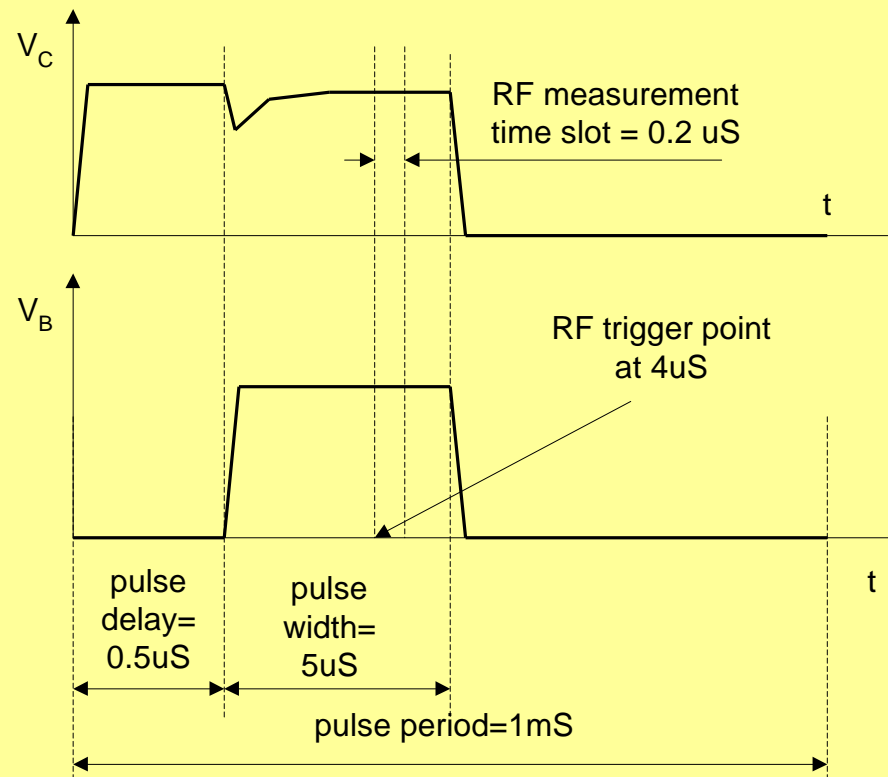
- DC Noise Level of HP85124 system, measured with open probes, is in the order of about +/- 50 uA

Plot PULSED\_dc/calibration/Pulse\_cal/VIR (On)



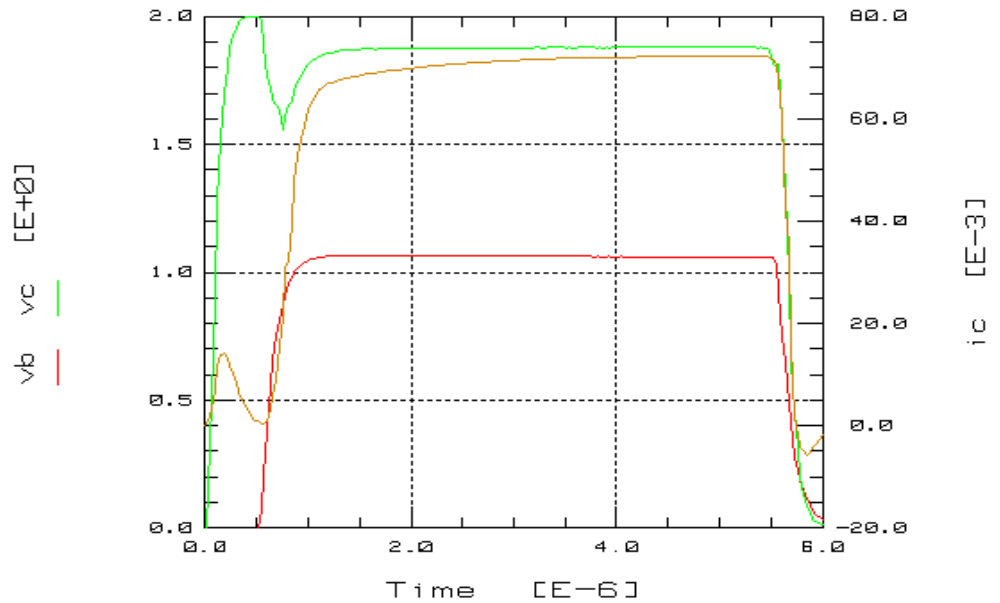
## Pulse time diagram, principle

- If  $V_B$  is switched on,  $V_C$  collapses first, and increases than again.
- A small ohmic voltage of about 0.2.V reduces than  $V_C$



# Real pulse time diagram

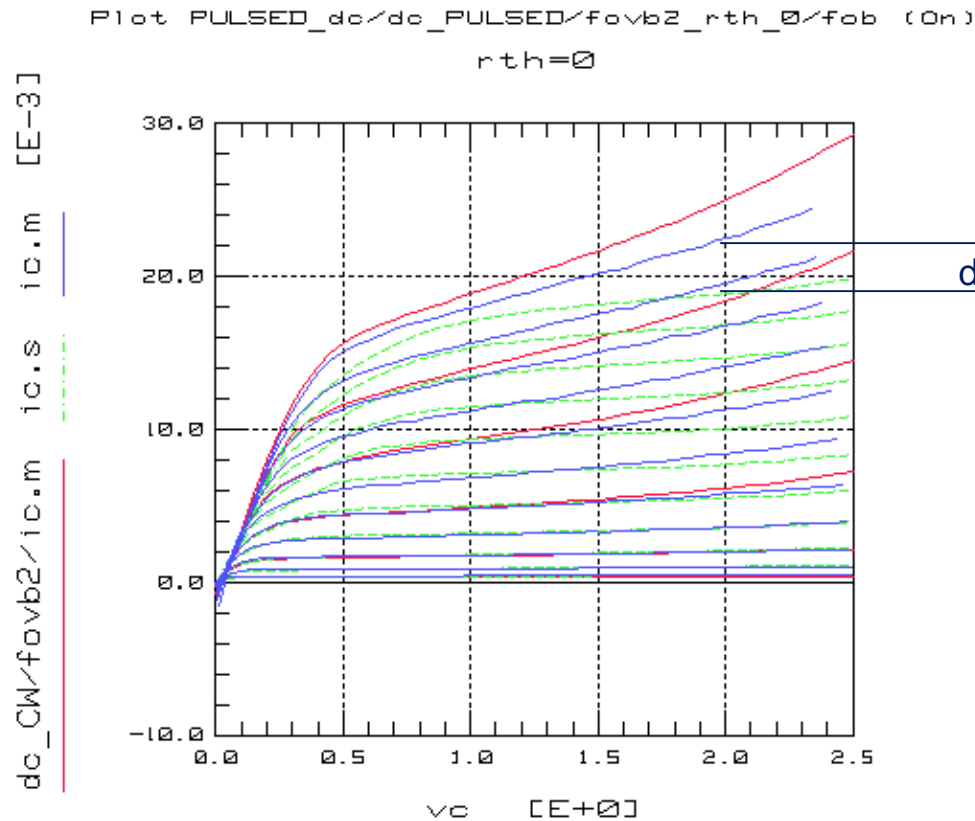
Plot: PULSED\_deimpulzed\_profile\VC2V\_vB1V1\_1ms\_5us5xpulse\_waveforms (On)



- green: collector voltage VC
- yellow collector current IC
- red: base voltage VB

- Used settings are: Pulse period = 10 mS
- VC: pulse width = 5.5  $\mu$ S, pulse delay = 0  $\mu$ S
- VB: pulse width = 5  $\mu$ S, pulse delay = 0.5  $\mu$ S
- DUT: b9c, n10b, trench isolated, Ae=2.8  $\mu$ m<sup>2</sup>, 4 in parallel

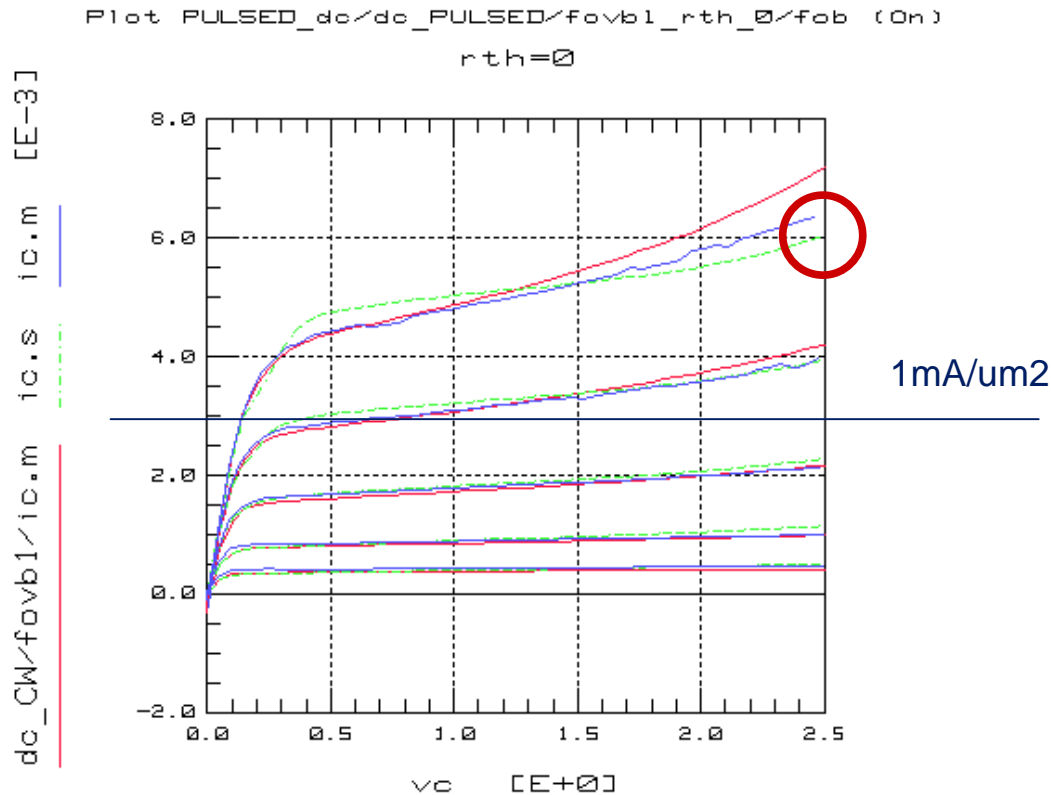
# Pulsed, non-pulsed and simulated output characteristics in comparison (1)



- red: CW, with self – heating
- blue: pulsed, no self – heating
- green: simulated, HICUM2.1, Spectre 4.4.6 (230203), RTH=0

- $V_B=0.85$  to  $1.1V$ , step=  $0.05V$ ,  $n=1$ ,  $A_e=2.8 \mu m^2$
- Problem: the simulation with  $RTH=0$  does not agree with the non-pulsed measurement

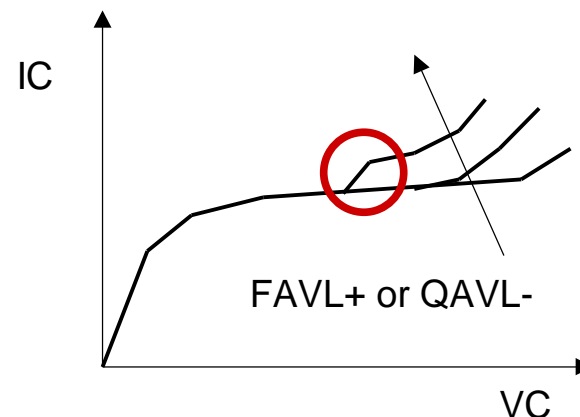
# Pulsed, non-pulsed and simulated output characteristics in comparison (2)



- $V_B=0.85$  to  $0.95V$ , step=  $0.025V$ ,  $n=1$ ,  $A_e=2.8 \mu m^2$
- Same picture at lower currents: the increase of simulated IC does not match the non-pulsed measurement

## Pulsed, non-pulsed and simulated output characteristics in comparison (3)

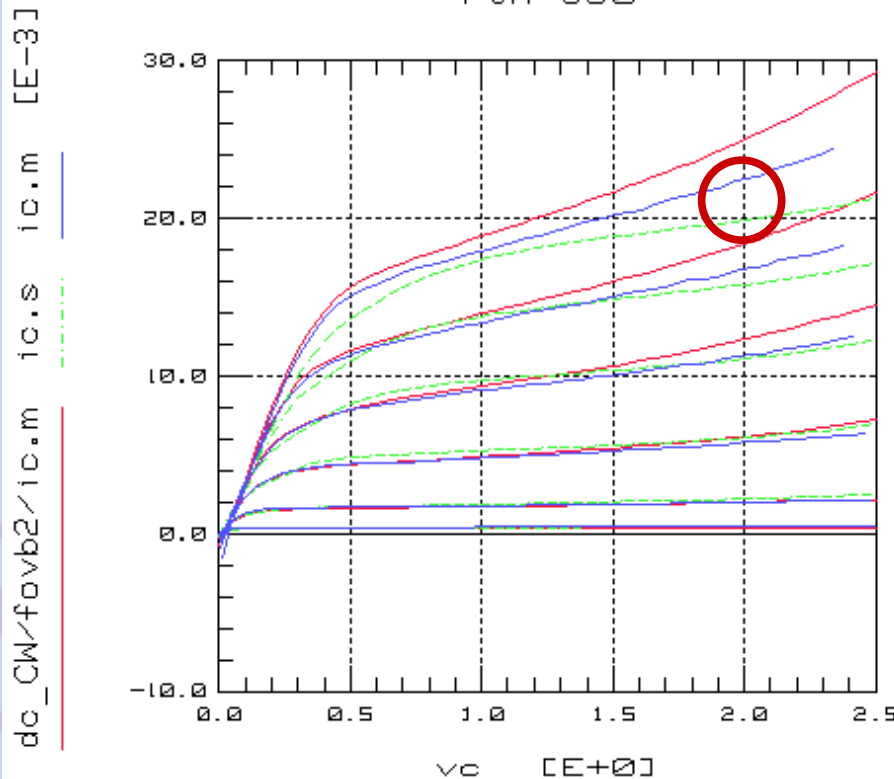
- Which model parameters are available to affect the increase of the output characteristic ?
- HJCI: the weighting factor for the inner BC charge, however, very high values are necessary (HJCI=10), but not reasonable, additional, HJCI is intended to fit in the LOW current range
- FAVL, QAVL: the avalanche parameters, however, high values of FAVL creates bumps etc., additional, convergence problems appear





# Pulsed, non-pulsed and simulated output characteristics in comparison (4)

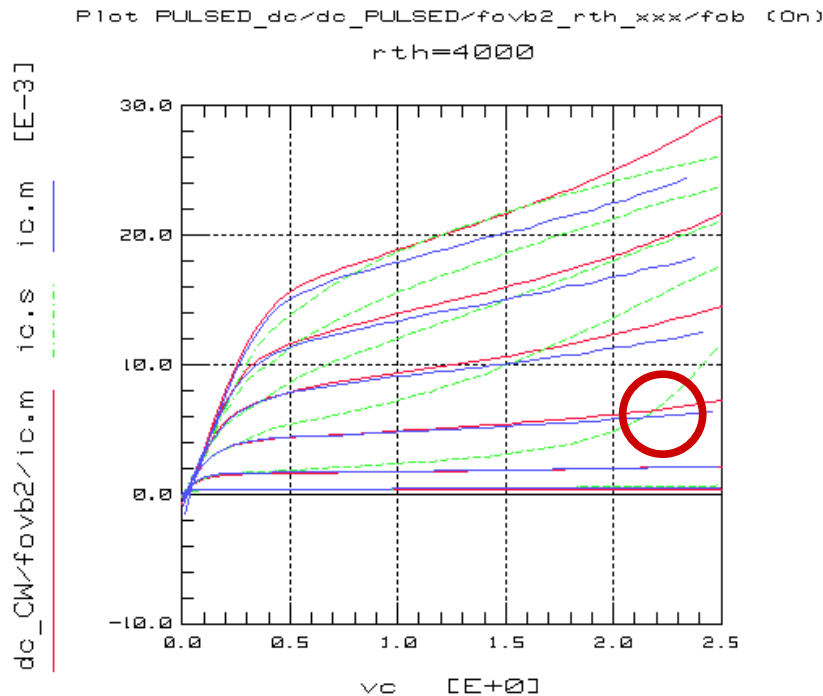
Plot PULSED\_dc/dc\_PULSED/fovb2\_rth\_XXX/fovb (On)  
rth=550



- red: CW, with self – heating
- blue: pulsed, no self – heating
- green: simulated, RTH=550, VGB=1.169, ALB=0.555m, ALTO=0.75m, KT0=4.8u, ZETARCX=0.372, ZETARBX=0.753

- $V_B=0.85$  to  $0.95V$ , step=  $0.025V$ ,  $n=1$ ,  $A_e=2.8 \mu m^2$
- Simulation using  $R_{TH}=550 K / W$  gives only a rough approximation for low currents, but not for high

# Pulsed, non-pulsed and simulated output characteristics in comparison (5)



- red: CW, with self – heating
- blue: pulsed, no self – heating
- green: simulated, RTH=4000, other see above

- $V_B=0.85$  to  $0.95V$ , step=  $0.025V$ ,  $n=1$ ,  $A_e=2.8 \mu m^2$
- $R_{TH}=4000 K / W$ , a typical value for trench isolated structures, gives a rough approximation for high currents, but overestimates the self heating at low currents.

## Pulsed, non-pulsed and simulated output characteristics in comparison (6)

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- Possible reason for the problem:
- The collector current at high  $V_B$  is affected both by self heating and the avalanche effect
- The avalanche model used in HICUM is sufficient for low current densities, but not for high
- If we try to model both effects with a high RTH value, an overestimated self heating at low current is the result
- Conclusion for this example: modeling the self heating using HICUM is restricted to current densities up to  $1 \text{ mA}/\mu\text{m}^2$